

At page 14, lines 10-11, please replace "132 to insulate the individual electrodes of the transistor devices" with --132. Further dopants may then be added to the diffusion or junction

B2 regions as desired.--

At page 14, line 13, please replace "illustrate" with --illustrates--.

At page 14, line 14, please replace "optimum" with --improved--.

At page 15, line 3, after "e.g.," please insert --a Fermi level of--.

At page 15, line 5, please replace "require" with --employ--.

At page 15, line 11, after "second metal", please insert --or other material--.

At page 16, line 9, please replace "device", both occurrences, with --transistor device--.

At page 16, line 11, please delete "metal".

At page 16, line 19, after "second metal", please insert --or other material--.

At page 16, line 23, please replace "utilize" with --utilizes a--.

At page 16, line 27, please replace "critical" with --important--.

At page 17, line 1, please replace "optimizing" with --improving--.

At page 17, line 20, please replace "i.e.," with --e.g., a Fermi level of--.

At page 18, lines 17, 20 and ^{18, 19}25, please replace "device" with --transistor device--.

At page 18, line 26, please replace "P-typed" with --P-type--.

At page 19, line 5, please replace "optimum" with --improved--.

IN THE ABSTRACT

At page 23, line 1, please insert --A method for making-- at the beginning of the paragraph.

IN THE CLAIMS

Please cancel claims 3-15.